

Silicon NPN Power Transistors

2SC3886A

DESCRIPTION

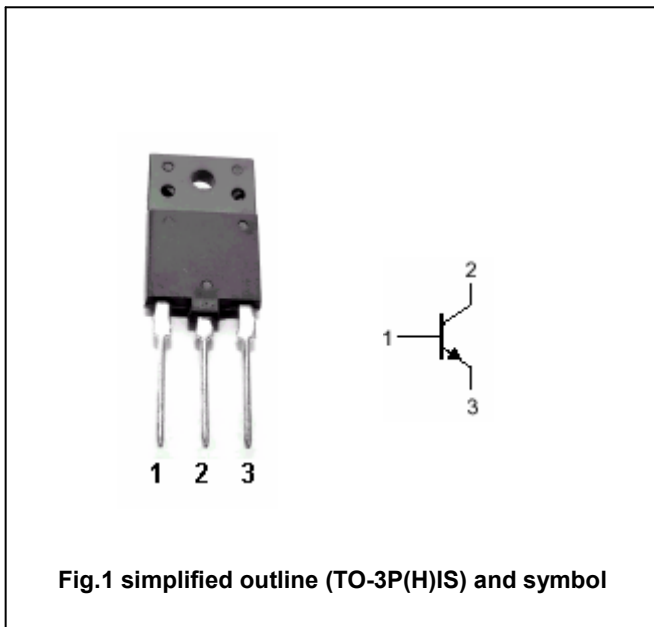
- With TO-3P(H)IS package
- High voltage ,high speed

APPLICATIONS

- Horizontal deflection output for high resolution display
- High speed switching regulator output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	600	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		8	A
I <sub>CM</sub>	Collector current-peak		15	A
I <sub>B</sub>	Base current		4	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	50	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =5mA ; I <sub>B</sub> =0	600			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =6A ; I <sub>B</sub> =1.5A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =6A ; I <sub>B</sub> =1.5A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =1500V; I <sub>E</sub> =0			1.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	8	15		
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =10V	1	3		MHz
C <sub>OB</sub>	Collector output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =10V; f=1MHz		210		pF
t <sub>s</sub>	Storage time	Resistive load I <sub>CP</sub> =6A ; I <sub>B1</sub> =-I <sub>B2</sub> =1.2A R <sub>L</sub> =33.3Ω			2.5	μs
t <sub>f</sub>	Fall time				0.15	μs

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PACKAGE OUTLINE

